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List of Publications by Year in descending order

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90
papers

3,656
citations

136885

32
h-index

133188

59
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91
all docs

91
docs citations

91
times ranked

3334
citing authors

#	ARTICLE	IF	CITATIONS
1	Systematic experimental and theoretical investigation of intersubband absorption in GaN/AlN quantum wells. <i>Physical Review B</i> , 2006, 73, .	1.1	239
2	InGaN/GaN Core-Shell Single Nanowire Light Emitting Diodes with Graphene-Based P-Contact. <i>Nano Letters</i> , 2014, 14, 2456-2465.	4.5	173
3	Flexible Light-Emitting Diodes Based on Vertical Nitride Nanowires. <i>Nano Letters</i> , 2015, 15, 6958-6964.	4.5	172
4	Integrated Photonic Platform Based on InGaN/GaN Nanowire Emitters and Detectors. <i>Nano Letters</i> , 2014, 14, 3515-3520.	4.5	171
5	GaN/AlN short-period superlattices for intersubband optoelectronics: A systematic study of their epitaxial growth, design, and performance. <i>Journal of Applied Physics</i> , 2008, 104, 093501.	1.1	165
6	Nanometer Scale Spectral Imaging of Quantum Emitters in Nanowires and Its Correlation to Their Atomically Resolved Structure. <i>Nano Letters</i> , 2011, 11, 568-573.	4.5	165
7	Ultraviolet Photodetector Based on GaN/AlN Quantum Disks in a Single Nanowire. <i>Nano Letters</i> , 2010, 10, 2939-2943.	4.5	155
8	GaN nanowire ultraviolet photodetector with a graphene transparent contact. <i>Applied Physics Letters</i> , 2013, 103, 201103.	1.5	136
9	Long-wavelength ($\lambda \sim 1.5 \mu\text{m}$) unipolar semiconductor laser in GaAs quantum wells. <i>Applied Physics Letters</i> , 1997, 71, 3619-3621.	1.5	134
10	Near infrared quantum cascade detector in GaN/AlGaIn heterostructures. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	116
11	Characterization and modeling of a ZnO nanowire ultraviolet photodetector with graphene transparent contact. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	106
12	Flexible White Light Emitting Diodes Based on Nitride Nanowires and Nanophosphors. <i>ACS Photonics</i> , 2016, 3, 597-603.	3.2	89
13	Terahertz intersubband absorption in GaN/AlGaIn step quantum wells. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	87
14	Intersubband spectroscopy of doped and undoped GaN/AlN quantum wells grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2003, 83, 5196-5198.	1.5	85
15	GaN/AlGaIn intersubband optoelectronic devices. <i>New Journal of Physics</i> , 2009, 11, 125023.	1.2	84
16	Core-shell InGaN/GaN nanowire light emitting diodes analyzed by electron beam induced current microscopy and cathodoluminescence mapping. <i>Nanoscale</i> , 2015, 7, 11692-11701.	2.8	70
17	Flexible Photodiodes Based on Nitride Core/Shell p-n Junction Nanowires. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 26198-26206.	4.0	66
18	Single-wire photodetectors based on InGaN/GaN radial quantum wells in GaN wires grown by catalyst-free metal-organic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	63

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19	Correlation of optical and structural properties of GaN/AlN core-shell nanowires. <i>Physical Review B</i> , 2011, 83, .	1.1	60
20	Single-Wire Light-Emitting Diodes Based on GaN Wires Containing Both Polar and Nonpolar InGaN/GaN Quantum Wells. <i>Applied Physics Express</i> , 2012, 5, 014101.	1.1	58
21	Short wavelength ($\lambda=2.13\mu\text{m}$) intersubband luminescence from GaN/AlN quantum wells at room temperature. <i>Applied Physics Letters</i> , 2007, 90, 121106.	1.5	56
22	GaN/AlGaIn waveguide quantum cascade photodetectors at $\lambda=1.55\mu\text{m}$ with enhanced responsivity and $\sim 40\text{GHz}$ frequency bandwidth. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	55
23	Short-wavelength intersubband electroabsorption modulation based on electron tunneling between GaN/AlN coupled quantum wells. <i>Applied Physics Letters</i> , 2007, 90, 223511.	1.5	54
24	Band offsets in cubic GaN/AlN superlattices. <i>Physical Review B</i> , 2011, 83, .	1.1	54
25	High-speed operation of GaN/AlGaIn quantum cascade detectors at $\lambda=1.55\mu\text{m}$. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	52
26	Two-color GaN/AlGaIn quantum cascade detector at short infrared wavelengths of 1 and $1.7\mu\text{m}$. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	52
27	Flexible inorganic light emitting diodes based on semiconductor nanowires. <i>Chemical Science</i> , 2017, 8, 7904-7911.	3.7	51
28	Intersubband absorption of cubic GaN/Al(Ga)N quantum wells in the near-infrared to terahertz spectral range. <i>Physical Review B</i> , 2011, 83, .	1.1	50
29	Electron confinement in strongly coupled GaN/AlN quantum wells. <i>Applied Physics Letters</i> , 2006, 88, 153113.	1.5	48
30	Photovoltaic properties of GaAsP core-shell nanowires on Si(001) substrate. <i>Nanotechnology</i> , 2012, 23, 265402.	1.3	45
31	Investigation of Photovoltaic Properties of Single Core-shell GaN/InGaIn Wires. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 21898-21906.	4.0	39
32	Experimental and theoretical analysis of transport properties of core-shell wire light emitting diodes probed by electron beam induced current microscopy. <i>Nanotechnology</i> , 2014, 25, 255201.	1.3	34
33	Interband and intersubband optical characterization of semipolar (112 $\bar{2}$)-oriented GaN/AlN multiple-quantum-well structures. <i>Applied Physics Letters</i> , 2008, 93, 111906.	1.5	32
34	Femto-second electron transit time characterization in GaN/AlGaIn quantum cascade detector at 1.5 micron. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	32
35	Double strain state in a single GaN/AlN nanowire: Probing the core-shell effect by ultraviolet resonant Raman scattering. <i>Physical Review B</i> , 2011, 83, .	1.1	32
36	Interplay of the photovoltaic and photoconductive operation modes in visible-blind photodetectors based on axial p-i-n junction GaN nanowires. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	30

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37	Photoluminescence polarization properties of single GaN nanowires containing $\text{Al}_x\text{Ga}_{1-x}\text{N}$ shells. Physical Review B, 2010, 81, .	1.1	28
38	A simplified GaN/AlGaIn quantum cascade detector with an alloy extractor. Applied Physics Letters, 2012, 101, .	1.5	28
39	In situ passivation of GaAsP nanowires. Nanotechnology, 2017, 28, 495707.	1.3	27
40	Green Electroluminescence from Radial <i>m</i> -Plane InGaIn Quantum Wells Grown on GaN Wire Sidewalls by Metal-Organic Vapor Phase Epitaxy. ACS Photonics, 2018, 5, 4330-4337.	3.2	26
41	Photoluminescence polarization in strained GaN/AlGaIn core/shell nanowires. Nanotechnology, 2012, 23, 325701.	1.3	25
42	Three-dimensional atomic-scale investigation of ZnO-MgxZn1-xO <i>m</i> -plane heterostructures. Applied Physics Letters, 2017, 111, .	1.5	24
43	Short infrared wavelength quantum cascade detectors based on <i>m</i> -plane ZnO/ZnMgO quantum wells. Applied Physics Letters, 2018, 113, .	1.5	24
44	Systematic study of near-infrared intersubband absorption of polar and semipolar GaN/AlN quantum wells. Journal of Applied Physics, 2013, 113, .	1.1	22
45	Color control of nanowire InGaIn/GaN light emitting diodes by post-growth treatment. Nanotechnology, 2015, 26, 465203.	1.3	22
46	Carrier localization in InN/InGaIn multiple-quantum wells with high In-content. Applied Physics Letters, 2012, 101, 062109.	1.5	20
47	Substrate-Free InGaIn/GaN Nanowire Light-Emitting Diodes. Nanoscale Research Letters, 2015, 10, 447.	3.1	19
48	Ultrafast relaxation and optical saturation of intraband absorption of GaN/AlN quantum dots. Applied Physics Letters, 2009, 94, .	1.5	18
49	InGaIn/GaN core/shell nanowires for visible to ultraviolet range photodetection. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 936-940.	0.8	18
50	Nanometer-scale monitoring of quantum-confined Stark effect and emission efficiency droop in multiple GaN/AlN quantum disks in nanowires. Physical Review B, 2016, 93, .	1.1	17
51	First demonstration of plasmonic GaN quantum cascade detectors with enhanced efficiency at normal incidence. Optics Express, 2014, 22, 21069.	1.7	14
52	Comprehensive analyses of core-shell InGaIn/GaN single nanowire photodiodes. Journal Physics D: Applied Physics, 2017, 50, 484001.	1.3	14
53	High Piezoelectric Conversion Properties of Axial InGaIn/GaN Nanowires. Nanomaterials, 2018, 8, 367.	1.9	14
54	Nanoscale electrical analyses of axial-junction GaAsP nanowires for solar cell applications. Nanotechnology, 2020, 31, 145708.	1.3	14

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55	Electroabsorption and refractive index modulation induced by intersubband transitions in GaN/AlN multiple quantum wells. <i>Optics Express</i> , 2012, 20, 12541.	1.7	13
56	A GaN/AlN quantum cascade detector with a broad response from the mid-infrared (4.1 μm) to the visible (550 nm) spectral range. <i>Applied Physics Letters</i> , 2020, 116, 171102.	1.5	13
57	Short-wave infrared ($\lambda = 3\text{--}4\text{ }\mu\text{m}$) intersubband polaritons in the GaN/AlN system. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	12
58	Optical properties of GaN nanowires grown on chemical vapor deposited-graphene. <i>Nanotechnology</i> , 2019, 30, 214005.	1.3	11
59	GaN/AlN quantum disc single-nanowire photodetectors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 1323-1327.	0.8	10
60	Nanoscale investigation of a radial p-n junction in self-catalyzed GaAs nanowires grown on Si (111). <i>Nanoscale</i> , 2018, 10, 20207-20217.	2.8	10
61	Electron beam induced current microscopy investigation of GaN nanowire arrays grown on Si substrates. <i>Materials Science in Semiconductor Processing</i> , 2016, 55, 72-78.	1.9	9
62	Probing elastic properties of nanowire-based structures. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	9
63	Colour optimization of phosphor-converted flexible nitride nanowire white light emitting diodes. <i>JPhys Photonics</i> , 2019, 1, 035003.	2.2	9
64	Correlated optical and structural analyses of individual GaAsP/GaP core-shell nanowires. <i>Nanotechnology</i> , 2019, 30, 304001.	1.3	7
65	Investigation of the effect of the doping order in GaN nanowire p-n junctions grown by molecular-beam epitaxy. <i>Nanotechnology</i> , 2021, 32, 085705.	1.3	7
66	Terahertz intersubband absorption of GaN/AlGaIn step quantum wells grown by MOVPE on Si(111) and Si(110) substrates. <i>Applied Physics Letters</i> , 2019, 115, .	1.5	6
67	Nitride Nanowires for Light Emitting Diodes. <i>Solid State Lighting Technology and Application Series</i> , 2019, , 425-484.	0.3	6
68	Correlated optical and electrical analyses of inhomogeneous core/shell InGaIn/GaN nanowire light emitting diodes. <i>Nanotechnology</i> , 2021, 32, 105202.	1.3	6
69	Nonlinear Absorption at Optical Telecommunication Wavelengths of InN Films Deposited by RF Sputtering. <i>IEEE Photonics Technology Letters</i> , 2012, 24, 1998-2000.	1.3	5
70	Investigation of GaN nanowires containing AlN/GaN multiple quantum discs by EBIC and CL techniques. <i>Nanotechnology</i> , 2019, 30, 214006.	1.3	5
71	Porous Nitride Light-Emitting Diodes. <i>ACS Photonics</i> , 2022, 9, 1256-1263.	3.2	5
72	Infrared photoluminescence of high In-content InN/InGaIn multiple-quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 17-20.	0.8	4

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73	Influence of surface passivation on the electrical properties of GaAsP nanowires. Applied Physics Letters, 2020, 117, 123104.	1.5	4
74	A 5.7 THz GaN/AlGaIn quantum cascade detector based on polar step quantum wells. Applied Physics Letters, 2022, 120, .	1.5	4
75	Cubic III-nitride coupled quantum wells towards unipolar optically pumped lasers. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 455-458.	0.8	3
76	Electromechanical conversion efficiency of GaN NWs: critical influence of the NW stiffness, the Schottky nano-contact and the surface charge effects. Nanoscale, 2022, 14, 4965-4976.	2.8	3
77	Flexible optoelectronic devices based on nitride nanowires embedded in polymer films. , 2016, , .		2
78	Intersubband absorption in m-plane ZnO/ZnMgO MQWs. Proceedings of SPIE, 2017, , .	0.8	2
79	Fabrication and Study of Optical Properties of LEDs Based on GaN Micropyramids with a Ni/Au/Graphene Semi-Transparent Contact. Technical Physics Letters, 2018, 44, 1111-1114.	0.2	2
80	Nitride nanowire light emitting diodes. , 2015, , .		1
81	Optical properties of photodetectors based on single GaN nanowires with a transparent graphene contact. Semiconductors, 2016, 50, 1097-1101.	0.2	1
82	InGaIn/GaN nanowire flexible light emitting diodes and photodetectors. , 2017, , .		1
83	Electroluminescence of Single InGaIn/GaN Micropyramids. Optics and Spectroscopy (English) Tj ETQq1 1 0.784314 rgBT /Overlock 10	0.2	1
84	Polarization-resolved photoluminescence study of an atom probe tip containing a ZnO-(Mg,Zn)O heterostructure. , 2022, , .		1
85	Electroabsorption and refractive index modulation induced by intersubband transitions in GaN/AlIn heterostructure waveguides. , 2013, , .		0
86	Optimization of the optical coupling in nanowire-based integrated photonic platforms by FDTD simulation. Beilstein Journal of Nanotechnology, 2018, 9, 2248-2254.	1.5	0
87	Flexible Light Emitting Diodes Based on Nitride Nanowires. , 2017, , .		0
88	Short infrared wavelength quantum cascade detectors based on non-polar ZnO/ZnMgO quantum wells. , 2019, , .		0
89	Nanoscale Electrical Characterization of Organized GaAsP Nanowires for Photovoltaic Energy Harvesting. , 2019, , .		0
90	Exciton ionization induced by intersubband absorption in nonpolar ZnO-ZnMgO quantum wells at room temperature. Physical Review B, 2022, 105, .	1.1	0